# BAS16VV; BAS16VY

# Triple high-speed switching diodes Rev. 02 — 10 September 2004

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

Three electrically isolated high-speed switching diodes, encapsulated in very small SMD plastic packages.

Table 1: **Product overview** 

Type number	Package		Configuration	
	Philips	EIAJ		
BAS16VV	SOT666	-	triple isolated diode	
BAS16VY	SOT363	SC-88	triple isolated diode	

#### 1.2 Features

- Very small SMD plastic packages
- High-speed switching
- Three electrically isolated diodes
- Low capacitance.

## 1.3 Applications

General purpose switching in surface mounted circuits.

#### 1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_R$	reverse voltage		-	-	100	V
$I_{FRM}$	repetitive peak forward current		-	-	450	mA
t <sub>rr</sub>	reverse recovery time		-	-	4	ns



## 2. Pinning information

Table 3: Discrete pinning

Pin	Description	Simplified outline	Symbol
1	anode (diode 1)		
2	anode (diode 2)	[6] [5] [4]	6 5 4
3	anode (diode 3)		
4	cathode (diode 3)		
5	cathode (diode 2)		1 2 3 sym043
6	cathode (diode 1)	001aab555	,

## 3. Ordering information

**Table 4: Ordering information** 

Type number	r Package		
	Name	Description	Version
BAS16VV	-	plastic surface mounted package; 6 leads	SOT666
BAS16VY	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

Table 5: Marking

Type number	Marking code [1]
BAS16VV	53
BAS16VY	16*

<sup>[1] \* =</sup> p: Made in Hong Kong

## 5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_R$	reverse voltage		-	100	V
l <sub>F</sub>	forward current		-	200	mA
I <sub>FRM</sub>	repetitive peak forward current		-	450	mA

<sup>\* =</sup> t: Made in Malaysia

<sup>\* =</sup> W: Made in China

Table 6: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward	square wave	<u>[1]</u> -		
	current	t <sub>p</sub> = 1 μs	-	4.5	Α
		$t_p = 1 \text{ ms}$	-	1	А
		t <sub>p</sub> = 1 s	-	0.5	А
P <sub>tot</sub>	total power dissipation				
	SOT666	T <sub>amb</sub> ≤ 25 °C	[2] [3]	180	mW
	SOT363	T <sub>sp</sub> = 85 °C	<u>[4]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup>  $T_i = 25$  °C prior to surge; see Figure 2.

## 6. Thermal characteristics

Table 7: Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
	SOT666		[1][2]	-	-	700	K/W
			[2] [3]	-	-	410	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point						
	SOT363		<u>[4]</u>	-	-	260	K/W

<sup>[1]</sup> Refer to SOT666 standard mounting conditions.

<sup>[2]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Single diode loaded.

<sup>[4]</sup> Solder points at pins 2, 3, 5 and 6.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 1 cm<sup>2</sup> collector mounting pad.

<sup>[4]</sup> Solder points at pins 2, 3, 5 and 6.



## 7. Characteristics

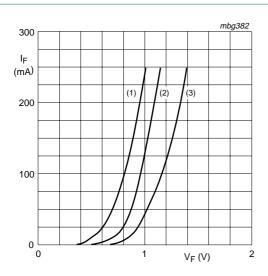
**Table 8: Characteristics** 

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol		Conditions	Min	Тур	Max	Unit
	Parameter	Conditions	IVIIII	чур	IVIAA	Oilit
Per diod	<b>e</b>					
$V_{F}$	forward voltage	see Figure 1				
		$I_F = 1 \text{ mA}$	-	-	715	mV
		$I_F = 10 \text{ mA}$	-	-	855	mV
		$I_F = 50 \text{ mA}$	-	-	1	V
		I <sub>F</sub> = 150 mA	-	-	1.25	V
I <sub>R</sub>	reverse current	see Figure 3				
		V <sub>R</sub> = 25 V	-	-	30	nΑ
		V <sub>R</sub> = 75 V	-	-	1	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	30	μΑ
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 0 \text{ V; } f = 1 \text{ MHz;}$ see Figure 4	-	-	1.5	pF
t <sub>rr</sub>	reverse recovery time	see Figure 5	<u>[1]</u> -	-	4	ns
$V_{fr}$	forward recovery voltage	see <u>Figure 6</u>	[2] _	-	1.75	V

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

<sup>[2]</sup> When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_i = 25 \,^{\circ}\text{C}$ ; typical values.
- (3)  $T_i = 25$  °C; maximum values.

Fig 1. Forward current as a function of forward voltage.

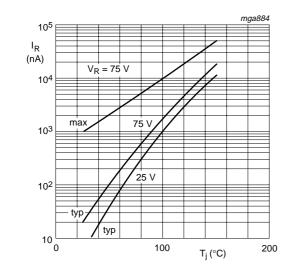
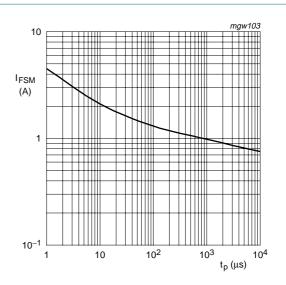


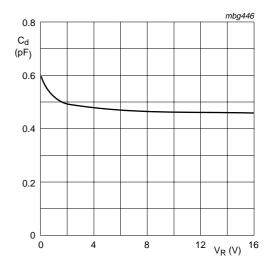
Fig 3. Reverse current as a function of junction temperature.



Based on square wave currents.

 $T_i = 25$  °C prior to surge.

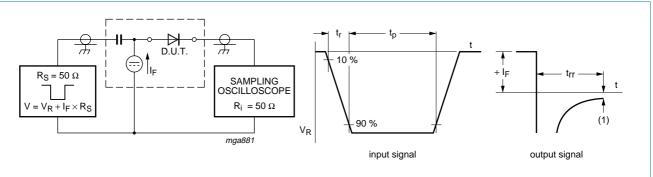
Fig 2. Maximum permissible non-repetitive peak forward current as a function of pulse duration.



f = 1 MHz;  $T_j = 25$  °C.

Fig 4. Diode capacitance as a function of reverse voltage; typical values.

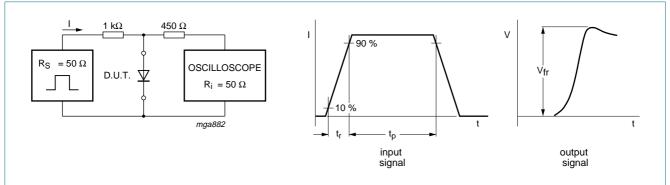
## 8. Test information



Input signal: Reverse pulse rise time  $t_r$  = 0.6 ns; reverse voltage pulse duration  $t_p$  = 100 ns; duty factor  $\delta \le$  0.05. Oscilloscope: Rise time  $t_r$  = 0.35 ns.

(1)  $I_R = 1 \text{ mA}$ .

Fig 5. Reverse recovery voltage test circuit and waveforms.



Input signal: Forward pulse rise time  $t_r$  = 20 ns; forward current pulse duration  $t_p \ge 100$  ns; duty factor  $\delta \le 0.005$ .

Fig 6. Forward recovery voltage test circuit and waveforms.

## 9. Package outline

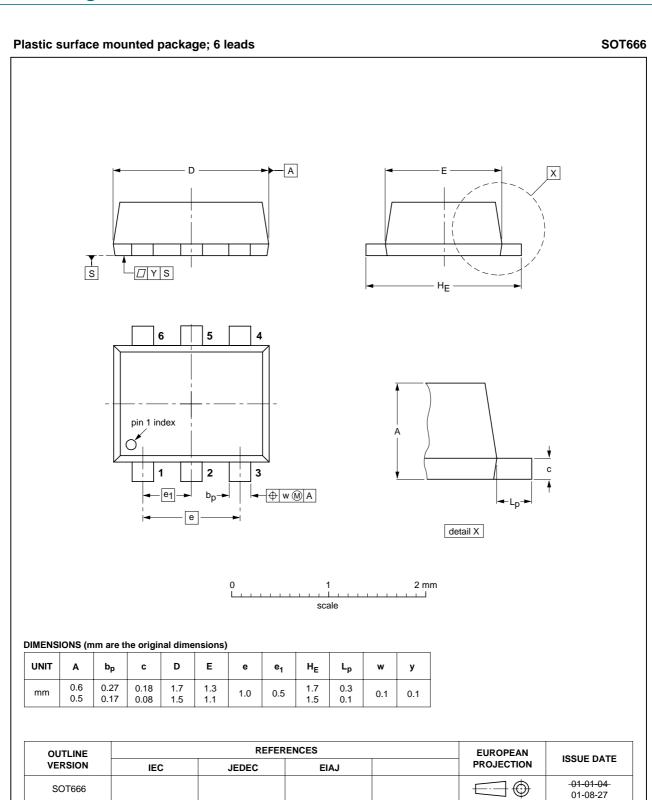


Fig 7. Package outline SOT666.

#### Plastic surface mounted package; 6 leads

#### **SOT363**

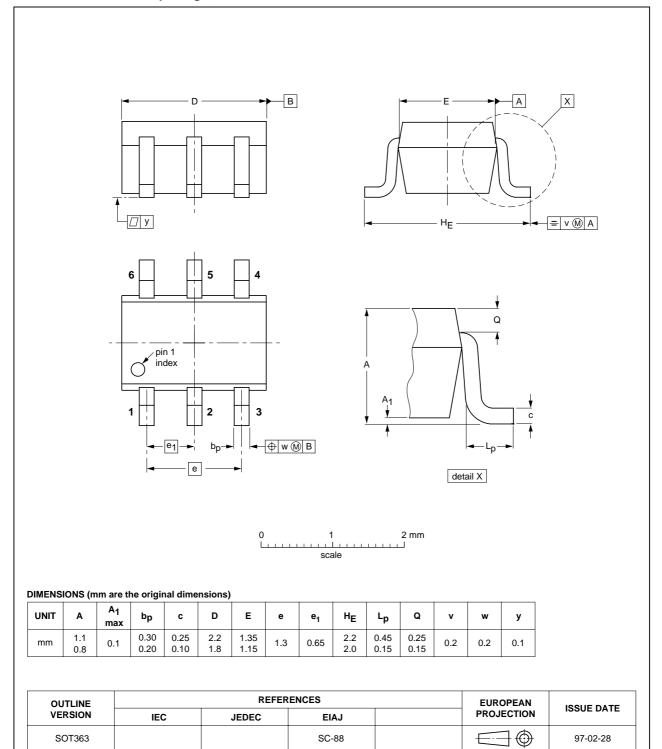


Fig 8. Package outline SOT363 (SC-88).



## 10. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity		
			3000	4000	10000
BAS16VV	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
BAS16VY	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125		-165

<sup>[1]</sup> For further information and the availability of packing methods, see Section 15.



## 11. Revision history

## Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes	
BAS16VV_BAS16VY_2	20040910	Product data sheet	-	9397 750 13856	BAS16VY_1	
Modifications:	information	<ul> <li>The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors.</li> <li>Type number BAS16VV added.</li> </ul>				
	71	Table 2 "Quick reference data": table added.				
	<ul> <li><u>Table 6 "Limiting values"</u>: maximum value of V<sub>RRM</sub> changed from 85 V to 100 V.</li> </ul>					
	<ul> <li><u>Table 6 "Limiting values"</u>: maximum value of V<sub>R</sub> changed from 75 V to 100 V.</li> </ul>					
BAS16VY_1	20030408	Product specification	-	9397 750 10909	-	



Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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## **Philips Semiconductors**

## BAS16VV; BAS16VY

Triple high-speed switching diodes

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